



# 考核报告

报告人: 翟明杰

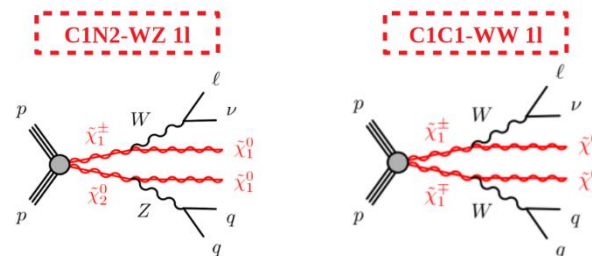
导师: Joao Guimaraes da Costa, 徐达

报告日期: 2022.09.02

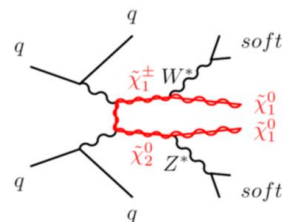
# 研究工作 (2022.5 – 2022.8)

## 1. ATLAS实验超对称 (SUSY) 寻找

### 1. 单轻子分析



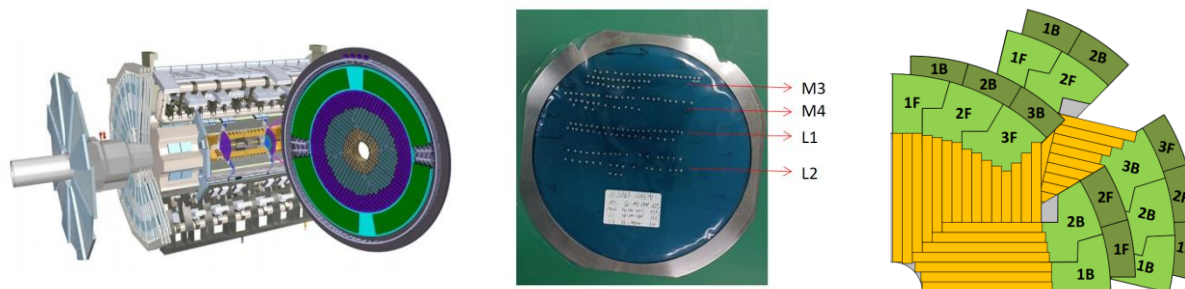
### 2. Compressed分析



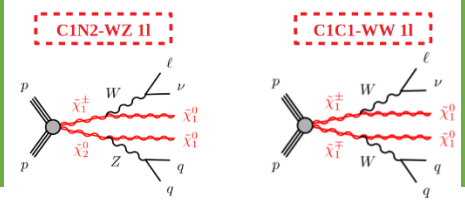
## 2. ATLAS实验高颗粒度时间探测器 (HGTD) 项目

### 1. NDL 传感器的性能研究

### 2. PEB (周边电子学)的性能研究



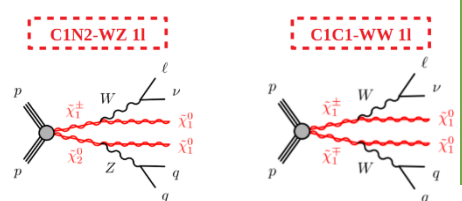
# 研究方向1-1: ATLAS SUSY 单轻子分析



## 该分析首次研究1L末态的gaugino $\rightarrow$ WW/WZ信号。

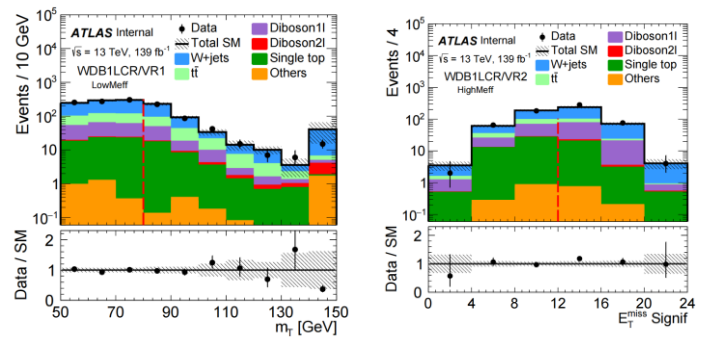
- 电弱相互作用的gaugino 通过 WW/WZ的衰变：
  - 该分析产生截面小/信号与SM本底类似 $\rightarrow$ challenge $\rightarrow$ 首次使用boost tagging技术
  - 末态: 1 lepton + 2-3 jets + MET
- 该分析于刚刚进行了最终的ATLAS审核, 预计下周发表公开的ATLAS note。作为分析最主力分析人员, 本人代表分析组进行**SUSY物理大组审核报告**和**ATLAS合作组审核报告**。
- 本人主要工作1: 负责新一轮systematic ntuple的产生和检验。
- 本人主要工作2: 对新的Sh2.2.11 V+jets样本进行研究：
  - 与旧的Sh2.2.1 V+jets 样本进行比较, 发现新的样本统计误差较小, 初选条件下, data/MC的符合程度较好。
  - 重新计算新样本各种理论误差。
- 本人主要工作3: 基于新的样本, 负责产生和分析所有的拟合结果。
  - Bkg-only fit: 对所有本底在控制区进行拟合, 检验拟合后不同区域的数据/MC符合程度。
  - Model-dependent fit: 对所有本底+信号在控制区+信号区进行拟合, 得出排除域。
  - Model-independent fit: 对所有本底+dummy信号在在控制区+信号区进行拟合, 得出dummy信号的上限。

# 研究方向1-1: ATLAS SUSY 单轻子分析

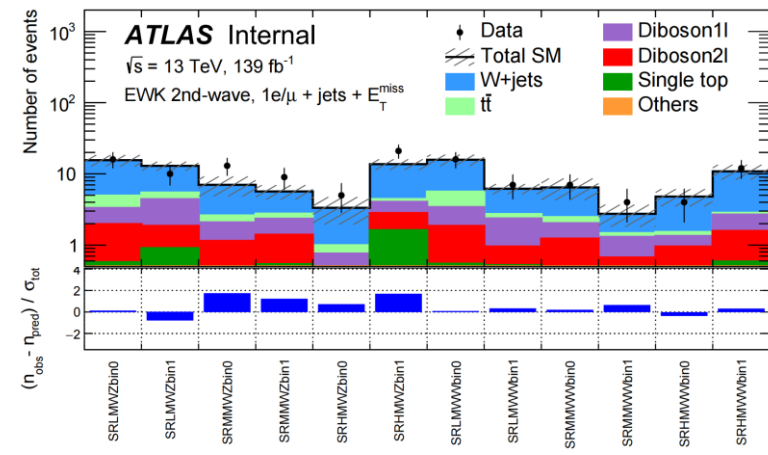
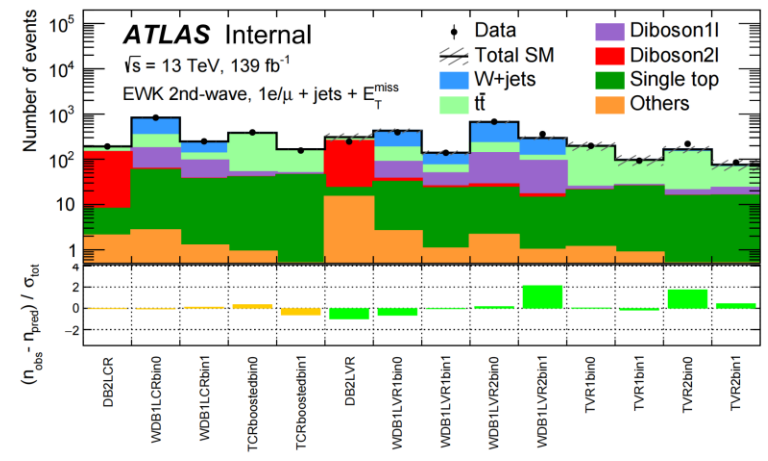
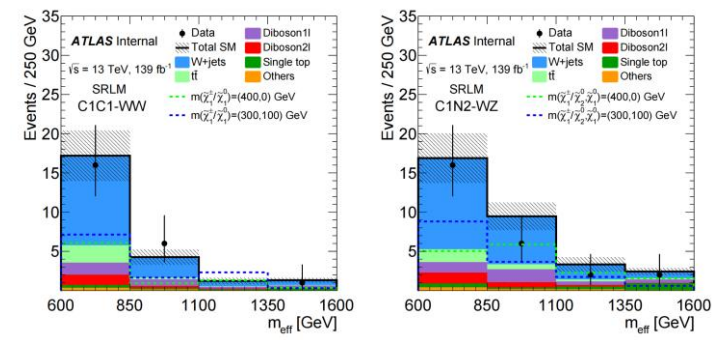


## bkg-only fit

$$\begin{aligned} \mu_{\text{DB2L}} &= 1.22^{+0.18}_{-0.18} \\ \mu_{\text{ttbar}} &= 0.81^{+0.10}_{-0.09} \\ \mu_{\text{WDB1L}} &= 1.05^{+0.09}_{-0.09} \end{aligned}$$

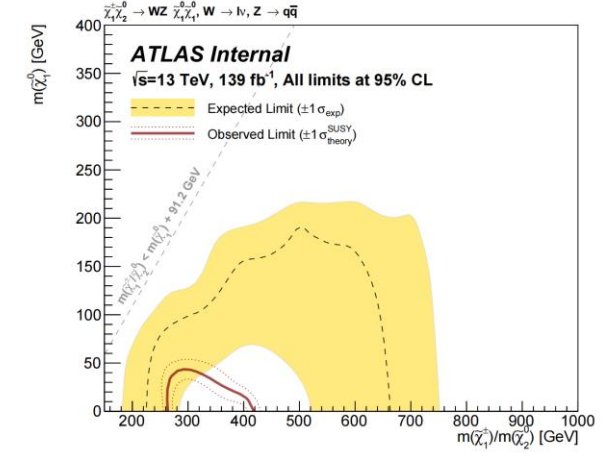
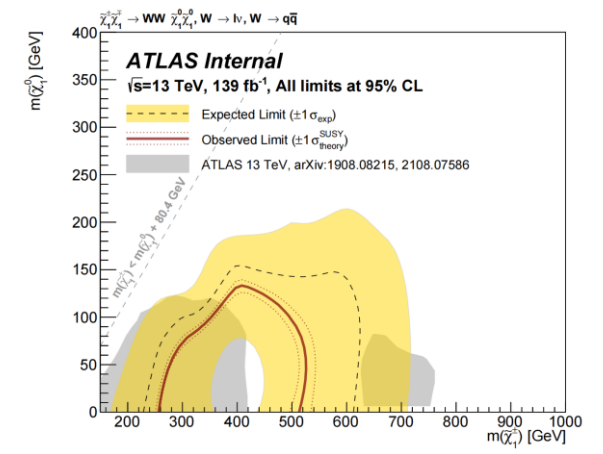


Data/MC在CR/VR符合程度很好。



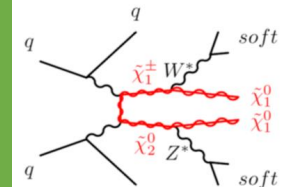
- ✓ C1C1\_WW的信号区里面，没有明显的超出。
- ✓ C1N2\_WZ的信号区里面，有一些小的超出(<2σ)。

## Model-dependent fit



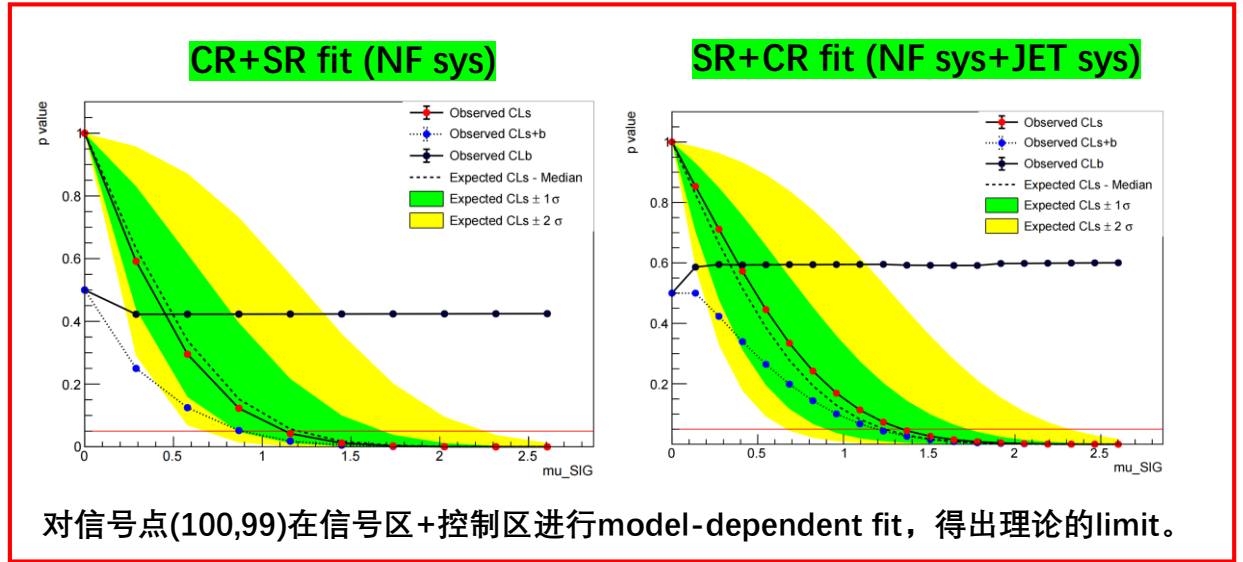
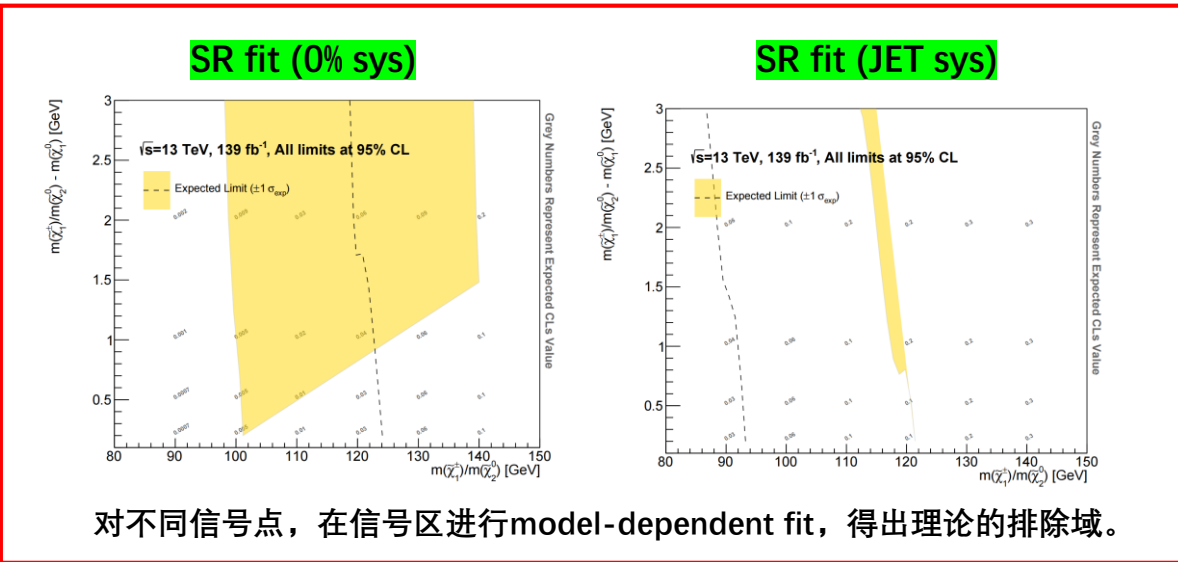
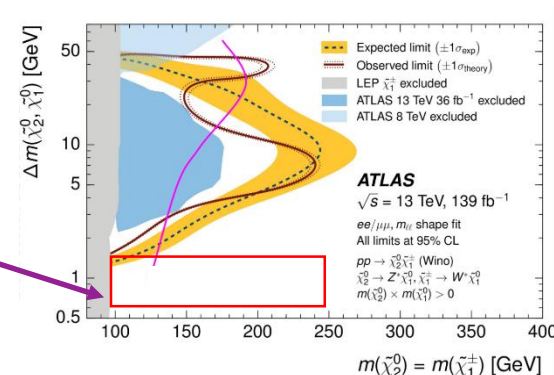
对于C1C1\_WW过程， $\tilde{\chi}_1^\pm$ 排除域相较于之前的结果提升了100GeV。

# 研究工作1-2: ATLAS SUSY Compressed分析

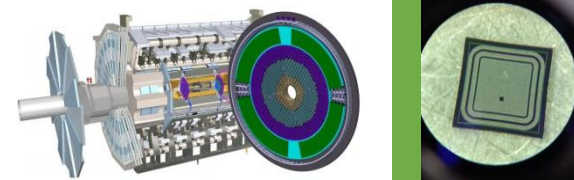


**该分析主要研究质量压缩的SUSY空间；是寻找Higgsino粒子最适合的研究和热门课题。**

- 研究目标：通过新“矢量玻色子融合VBF进程”进一步拓展 $\Delta M < 1\text{GeV}$ 空间。
  - 质量压缩空间的末态粒子动量很低->难以重建
  - 标记两个VBF jets->触发事例
  - 末态：2 VBF jets + MET (0 轻子)
- 该分析已于2021.06.11完成ATLAS的Partial Analysis Review；计划于明年发表。
- 本人目前担任该分析主要分析人员。
- 主要工作1：对信号区的信号显著性进行研究。
- 主要工作2：对QCD本底过程进行估计。

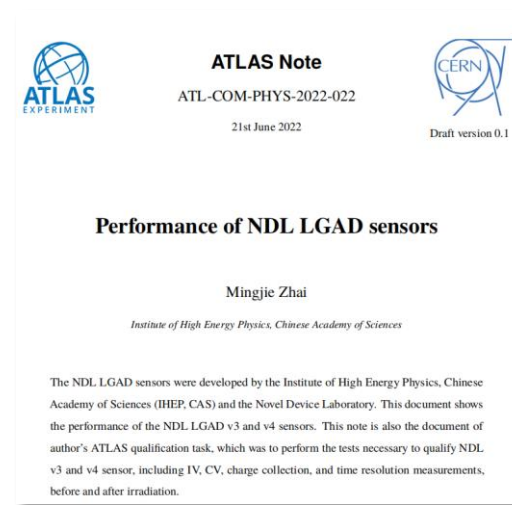


# 研究方向2-1: NDL\_v4传感器性能研究



NDL传感器是高能所联合北师大设计制作的一款用于HGTD探测器的LGAD传感器。

- NDL第四版传感器包括三种不同注入的设计(高注入的过早击穿, 主要研究低、中注入),本人负责对其进行性能的研究。
- 主要工作1: 完成了辐照后的性能测试
  - 低温的IV测试。
  - 常温下CV测试。(上次考核已汇报)
  - 低温的beta测试, 得出传感器的电荷收集和时间分辨等性能。
- 主要工作2: 汇总NDL第三版和第四版传感器研究成果。
  - 将全部的研究成果总结到ATLAS COM note里面。
  - 在HGTD long week里面总结汇报所有成果, 顺利完成了本人的qualification task。



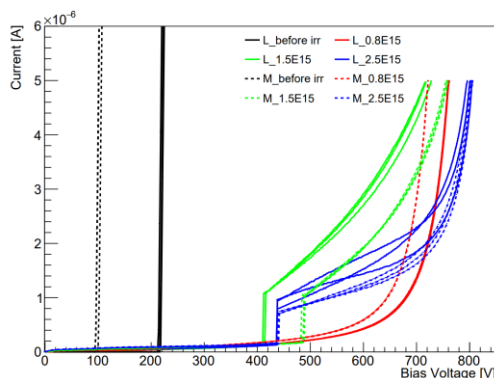
Mingjie Zhai

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Physics PhD student  
Beijing IHEP  
Institute of High Energy Physics, Chinese Academy of Sciences

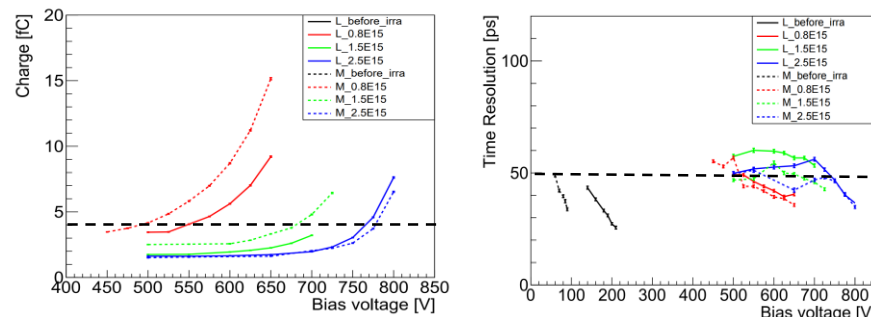
Active Author  
Operation Tasks (Student)

低温下的IV研究



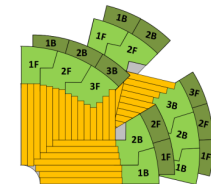
✓ 辐照之后, 漏电流增大, 击穿电压变高。

低温下的beta测试

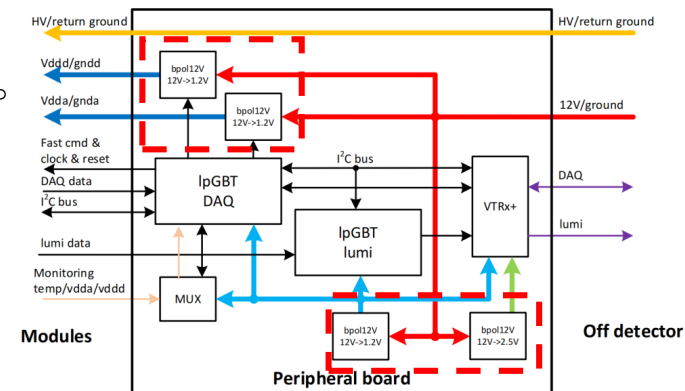


- ✓ 辐照剂量较低时, 中注入的传感器性能更好。剂量提高后, 中注入和低注入的性能接近。
- ✓ 结论: 通过提高注入的方法, 不能有效提高传感器的抗辐照性能。

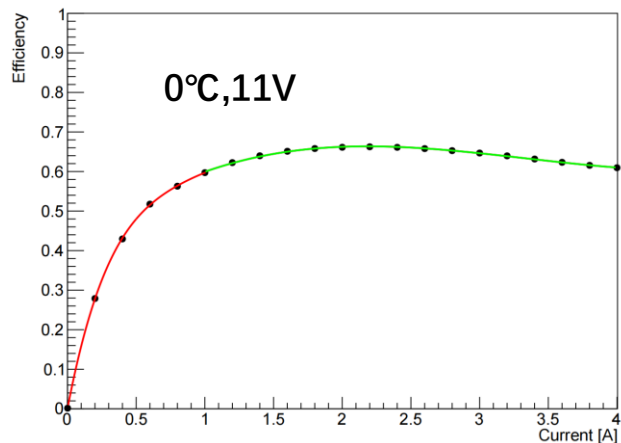
# 研究方向2-2: PEB(周边电子学)的性能研究



- BPOL12V可以把12V的电压转化成1.2V或2.5V的电压，进而给module和PEB的其他部件供电。
- 通过对BPOL12V的效率进行研究，有利于各部件的散热和电流输入进行优化。
- **本人主要工作：研究BPOL12V的效率和输出电流、输入电压、温度的之间关系。**
- 下一步：对BPOL12V的效率进行多维拟合，同时测量并收集更多的数据。



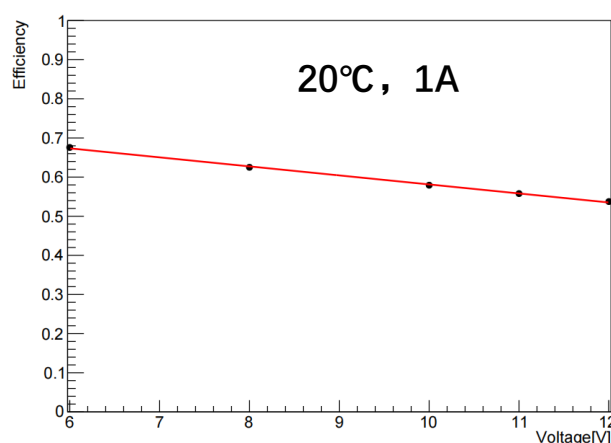
效率 - 输出电流



$$Eff = p_0 + p_1 I + p_2 I^2 + p_3 I^3 + p_4 I^4 \quad (0A < I < 1A)$$

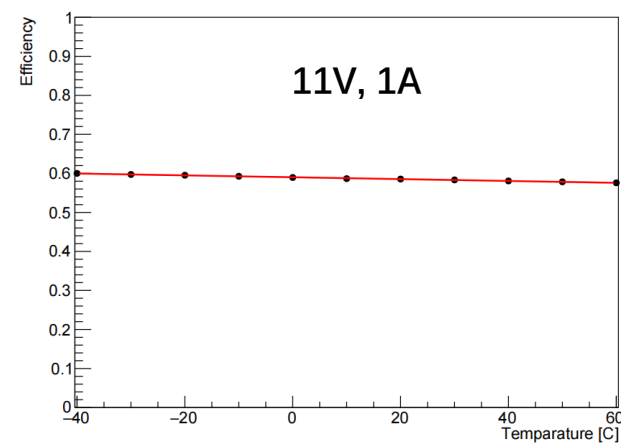
$$Eff = p_0 + p_1 I + p_2 I^2 + p_3 I^3 \quad (1A < I < 4A)$$

效率 - 输入电压



$$Eff = p_0 + p_1 V$$

效率 - 温度



$$Eff = p_0 + p_1 T$$

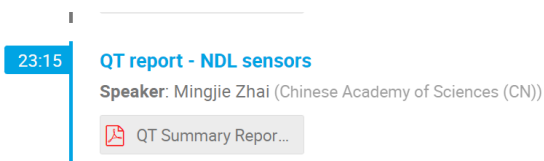
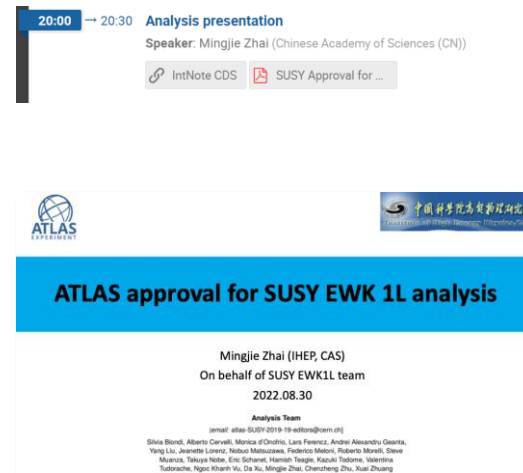
# 总结与展望

## ➤ 超对称物理探寻:

- 担任**SUSY 1L分析的最主力分析人员**和**SUSY compressed组分析的主力分析人员**。数次在这两个分析的组会作报告，同时在会议上给出**重要**报告如下：
  - 代表EWK 1L 组进行**SUSY approval**报告: <https://indico.cern.ch/event/1177814/>
  - 代表EWK 1L 组进行**ATLAS approval**报告: <https://indico.cern.ch/event/1194429/>
- 下一步: 推动以上两分析, 1L分析预计下周发表ATLAS CONF Note (**ATLAS-CONF-2022-059**), 年底发表一篇期刊文章。Compressed分析预计明年发表一篇文章。

## ➤ HGTD 研究:

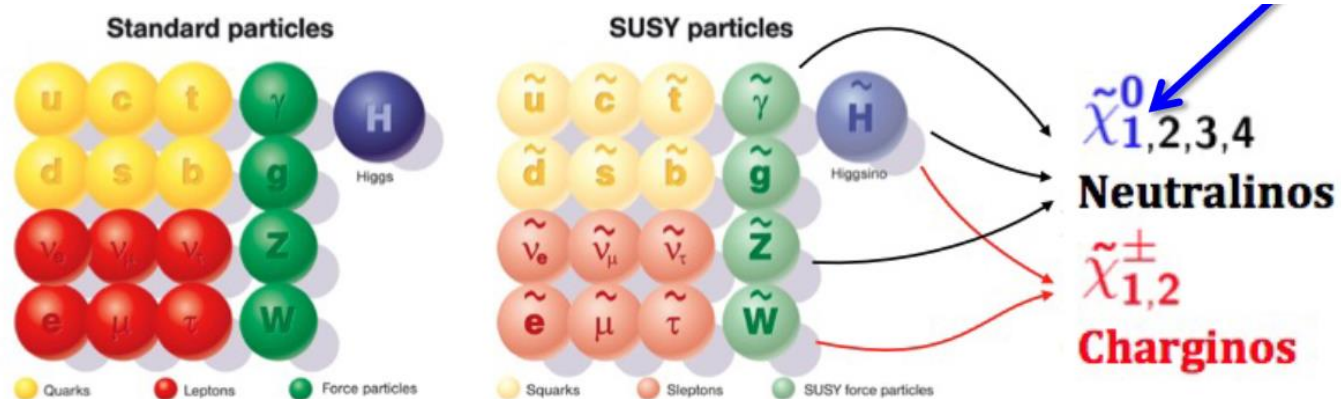
- 本人对新一版的NDL传感器进行辐照前后IV、CV、电荷收集、时间分辨等性能的研究。
  - 在**ATLAS HGTD long week**汇报了本人所有的NDL sensor的研究结果 (<https://indico.cern.ch/event/1127322/#128-qt-report-ndl-sensors>), 并将所有结果总结在 **ATL-COM-HGTD-2022-023**中。顺利完结了本人的qualification task。
- 正在进行PEB BPOL12V的效率研究。
- 下一步: 继续参与PEB的研究工作。





# Backup

# 超对称简介



## Bino LSP



## Higgsino LSP



## Wino LSP



# ATLAS SUSY Compressed分析 --- region

## ➤ **0L Preselection:**

- Passes MET trigger
- MET > 200 GeV
- Valid VBF tag(i.e. at least 2 non-btagged jets with pt > 30, eta < 5 that have eta1 \* eta2 < 0)
- M\_jj > 500 GeV
- nLep\_signal = 0

## **SR**

- nLep\_signal == 0
- trigMatch\_metTrig == 1
- vbfjjM > 1000
- vbfTagJet1\_Pt > 80
- vbfTagJet2\_Pt > 80
- vbfjjDEta > 3
- vbfjjDPhi < 2
- minDPhiAllJetsMet > 0.6
- nBJet20 == 0
- nJets = {2,3,4}
- Met = {200,225,250,275,300,325,350,375,400,425,450,475,500,525,550,600,700,+∞}

## **WCR**

- nLep\_signal == 1
- trigMatch\_singleElectronTrig == 1||  
trigMatch\_singleMuonTrig == 1
- vbfjjM > 1000
- vbfTagJet1\_Pt > 80
- vbfTagJet2\_Pt > 80
- vbfjjDEta > 3
- vbfjjDPhi < 2
- minDPhiAllJetsMet\_LepInvis > 0.6
- nBJet20 == 0
- nJets = {2,3,4}
- met\_Et\_LepInvis > 200

## **ZCR**

- nLep\_signal == 2
- trigMatch\_diElectronTrig == 1||  
trigMatch\_diMuonTrig == 1
- vbfjjM > 1000
- vbfTagJet1\_Pt > 80
- vbfTagJet2\_Pt > 80
- vbfjjDEta > 3
- vbfjjDPhi < 2
- minDPhiAllJetsMet\_LepInvis > 0.6
- nBJet20 == 0
- nJets = {2,3,4}
- met\_Et\_LepInvis > 200

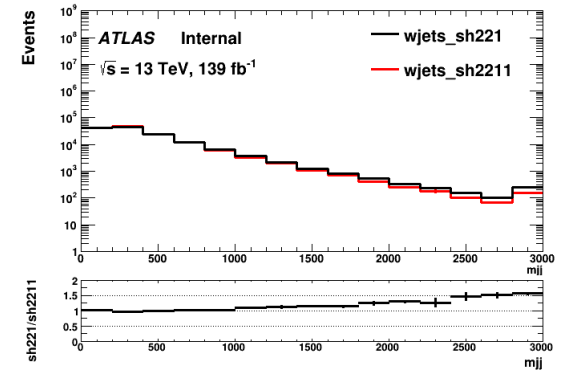
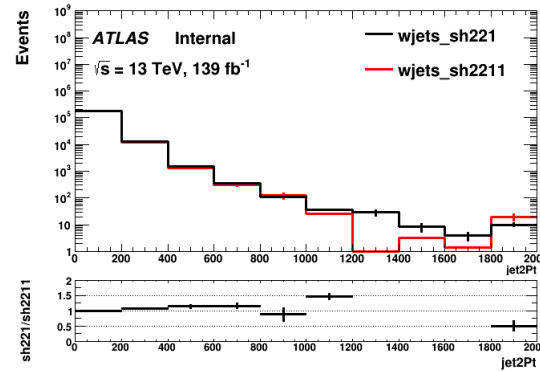
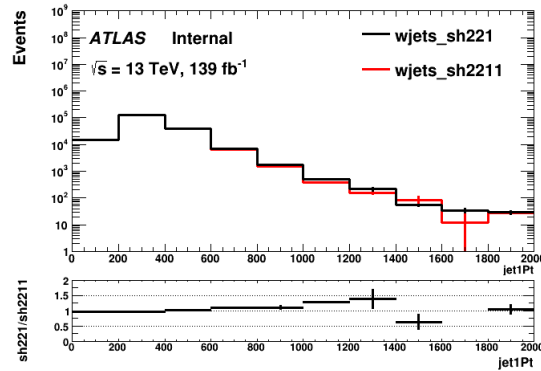
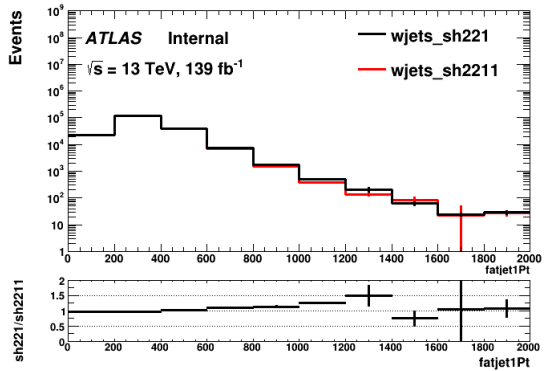
# ATLAS SUSY 单轻子分析 --- region

Variable	C1C1-WW model			C1N2-WZ model		
	SRLM	SRMM	SRHM	SRLM	SRMM	SRHM
$N_{\text{lep}} (p_T > 25 \text{ GeV})$				1		
$N_{\text{jet}} (p_T > 30 \text{ GeV})$				1 - 3		
$N_{\text{large-Rjet}} (p_T > 250 \text{ GeV})$				$\geq 1$		
$E_T^{\text{miss}} [\text{GeV}]$				$> 200$		
$\Delta\phi(\ell, E_T^{\text{miss}})$				$< 2.6$		
large-R jet type	W-tagged			Z-tagged		
$m_T [\text{GeV}]$	120-200	200-300	$> 300$	120-200	200-300	$> 300$
Exclusion SR						
$m_{\text{eff}} [\text{GeV}]$ (excl.)	[600-850, $> 850$ ]			[600-850, $> 850$ ]		
$m_{\text{ij}} [\text{GeV}]$ (excl.)	[70-90, -]			[80-100, -]		
$\sigma_{E_T^{\text{miss}}} \text{ (excl.)}$	$[> 12, > 15]$			$[> 12, > 12]$		
Discovery SR						
$m_{\text{eff}} [\text{GeV}]$ (disc.)	$> 600$	$> 600$	$> 850$	$> 600$	$> 850$	$> 850$
$m_{\text{ij}} [\text{GeV}]$ (disc.)	-	-	-	80-100	-	-
$\sigma_{E_T^{\text{miss}}} \text{ (disc.)}$	$> 15$	$> 15$	$> 15$	$> 12$	$> 12$	$> 12$

Variable	WDB1L and T		
	CR	VR1	VR2
$N_{\text{lep}} (p_T > 25 \text{ GeV})$	1		
$N_{\text{jet}} (p_T > 30 \text{ GeV})$	1 - 3		
$N_{\text{b-jet}} (p_T > 30 \text{ GeV})$	0 for WDB1L; $> 0$ for Top		
$N_{\text{large-Rjet}} (p_T > 250 \text{ GeV})$	$\geq 1$		
$E_T^{\text{miss}} [\text{GeV}]$	$> 200$		
$\Delta\phi(\ell, E_T^{\text{miss}})$	$< 2.9$		
large-R jet type	W-tagged		
$m_{\text{eff}} [\text{GeV}]$	[600-850, $> 850$ ]		
$\sigma_{E_T^{\text{miss}}}$	$< 12$	$< 12$	$> 12$
$m_T [\text{GeV}]$	50 - 80	$> 80$	50 - 120

Variable	DB2L	
	CR	VR
$N_{\text{lep}} (p_T > 25 \text{ GeV})$	2	
$N_{\text{jet}} (p_T > 30 \text{ GeV})$	1 - 3	
$N_{\text{b-jet}} (p_T > 30 \text{ GeV})$	0	
$E_T^{\text{miss}} [\text{GeV}]$	$> 200$	
$\Delta\phi(\ell, E_T^{\text{miss}})$	$< 2.9$	
$m_{\ell\ell} [\text{GeV}]$	70 - 100	
$m_{\text{ij veto}} [\text{GeV}]$	75 - 95	
$\sigma_{E_T^{\text{miss}}}$	$> 12$	$> 10$
$m_T [\text{GeV}]$	50 - 200	200 - 350

# ATLAS SUSY 单轻子分析 --- Sh221 vs Sh2211

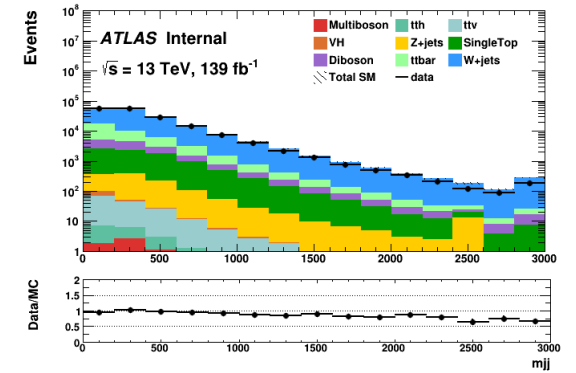
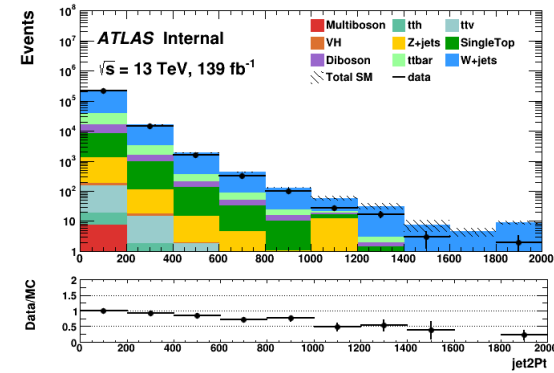
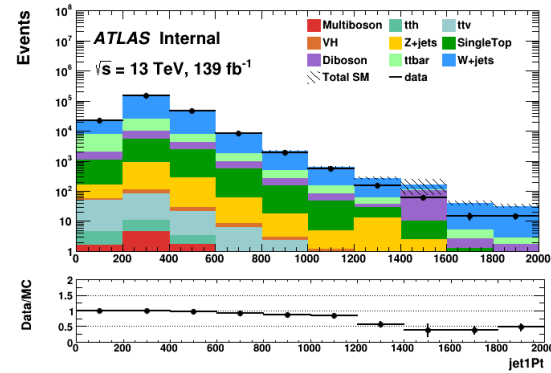
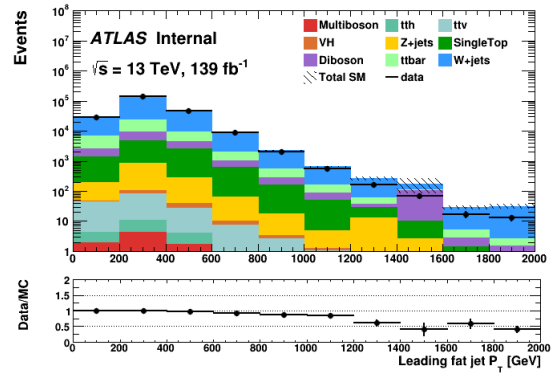


	raw	weighted
wjets_sh2211	5965846	$192020 \pm 244$
wjets_sh221	2310017	$190936 \pm 473$

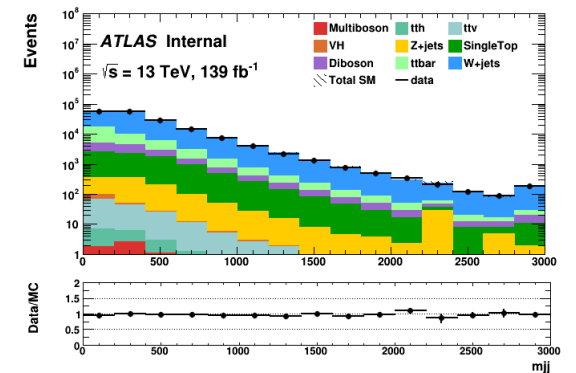
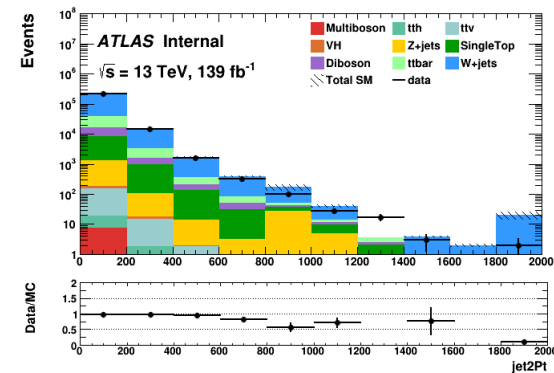
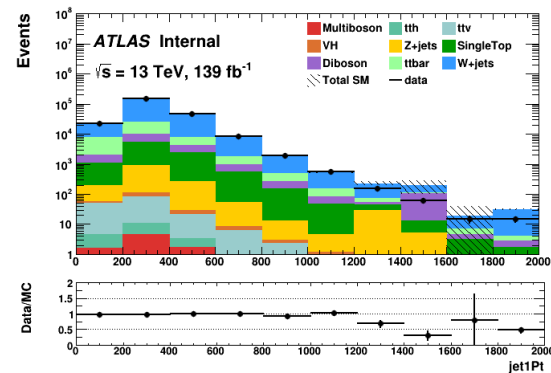
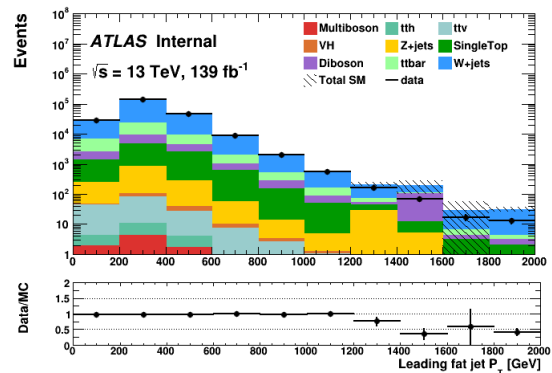
- At preselection level, Sh2.2.11 has lower estimation comparing to Sh2.2.1 in high jet Pt region ( $>400\text{GeV}$ ).
- The conclusion agrees with the discussion in [note](#).
- Sh2.2.11 has 2.6 times more stats than Sh2.2.1.

# ATLAS SUSY 单轻子分析 --- Sh221 vs Sh2211

## Sh2.2.1 for V+jets

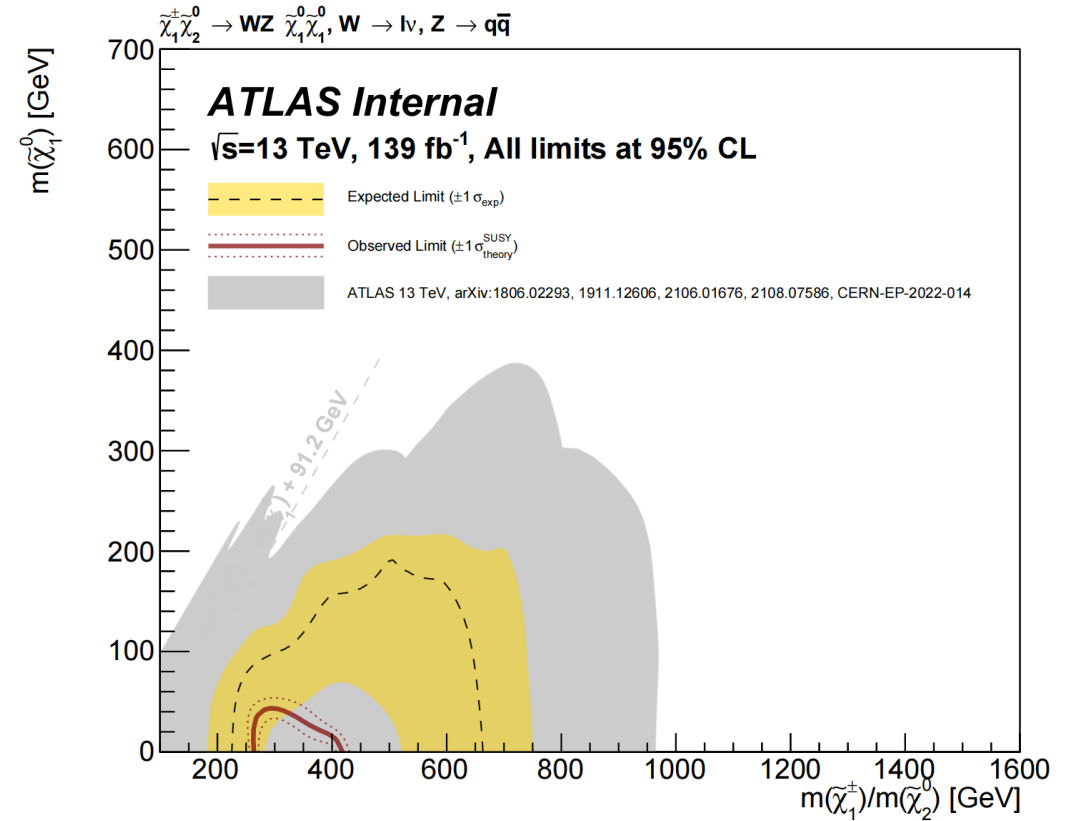
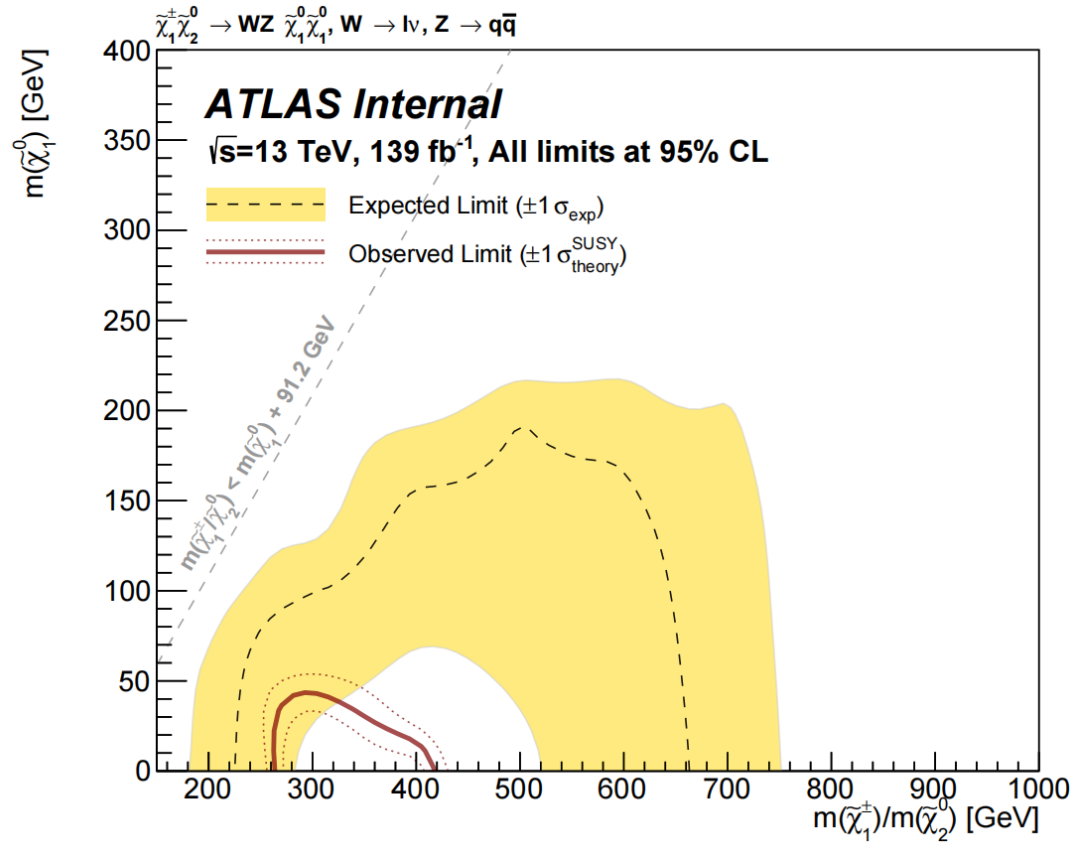


## Sh2.2.11 for V+jets



Improved data/MC agreement in high jet Pt region (esp. 400-1200GeV.)

# ATLAS SUSY 单轻子分析 --- Limit (C1N2-WZ)



# ATLAS HGTD sensor Specifications

Technology	Silicon Low Gain Avalanche Detector (LGAD)
Pad size	1.3 × 1.3 mm <sup>2</sup>
Pad array (rows × columns)	15 × 15
Substrate	p-type
Thickness (D)	50±5 μm (active), 300±30 μm (total)
HV biasing	back side
Time resolution	~35 ps at V <sub>op</sub> (as produced)
Charge collection	>15 fC at V <sub>op</sub> (as produced)
<b>Passivation thickness</b>	between 0.8 μm and 5 μm
<u>Bump-bonding pad opening</u>	90 μm diameter
<u>Bump-bonding pad size</u>	95 μm diameter
<u>Inactive edge</u>	<300 μm
<u>Dicing chipping</u>	<20 μm
<u>Dicing line</u>	80 μm
Target pad capacitance	<4.5 pF (backplane+inter-pad)
Gain layer depletion (V <sub>gl</sub> )	< 60 V
Full depletion (V <sub>fd</sub> )	< V <sub>gl</sub> + 90 V
Breakdown voltage (V <sub>bd</sub> ) (-30°C)	(V <sub>bd</sub> -V <sub>gl</sub> )/D>0.7 V/μm, V <sub>bd</sub> >V <sub>fd</sub> +30 V
Breakdown condition (-30°C)	>200 nA/pad
Device leakage current (-30°C)	< 2 μA/cm <sup>2</sup> at V <sub>op</sub> (~35 ps, >15 fC)
Pad leakage current (-30°C)	< 200 nA at V <sub>op</sub> (~35 ps, >15 fC)
Inter-pad gap (IP)	40 μm < IP < 100 μm (region with <4 fC , time resolution < 50 ps)
Fraction of good sensors per wafer (all pads within specifications)	70 % if the UBM is not done at fabrication site
Optical inspection	no stains, residues or scratches on sensor area.

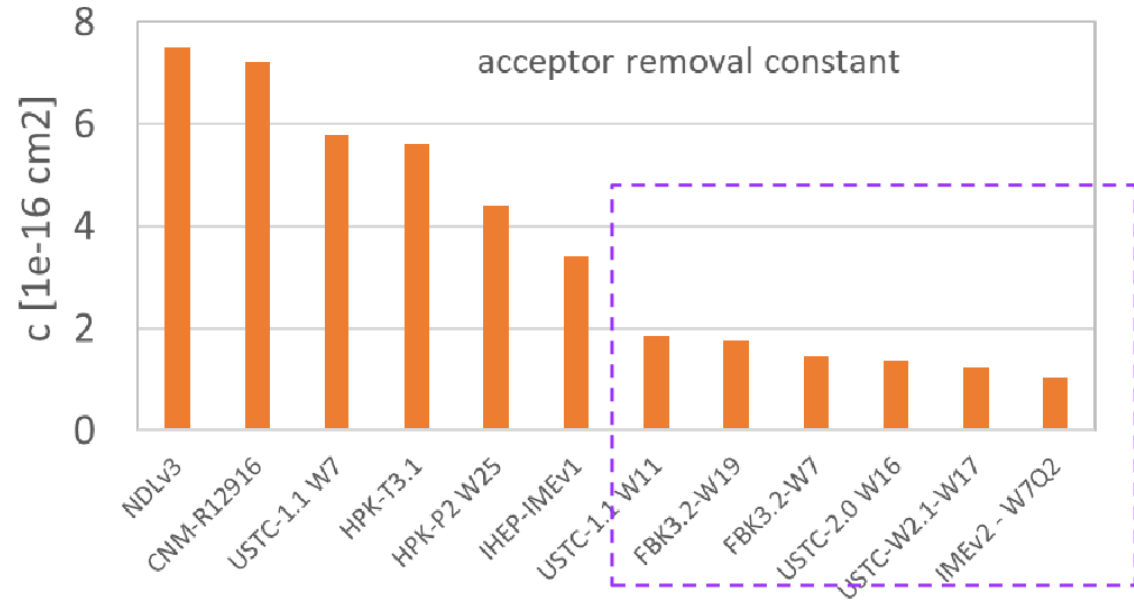
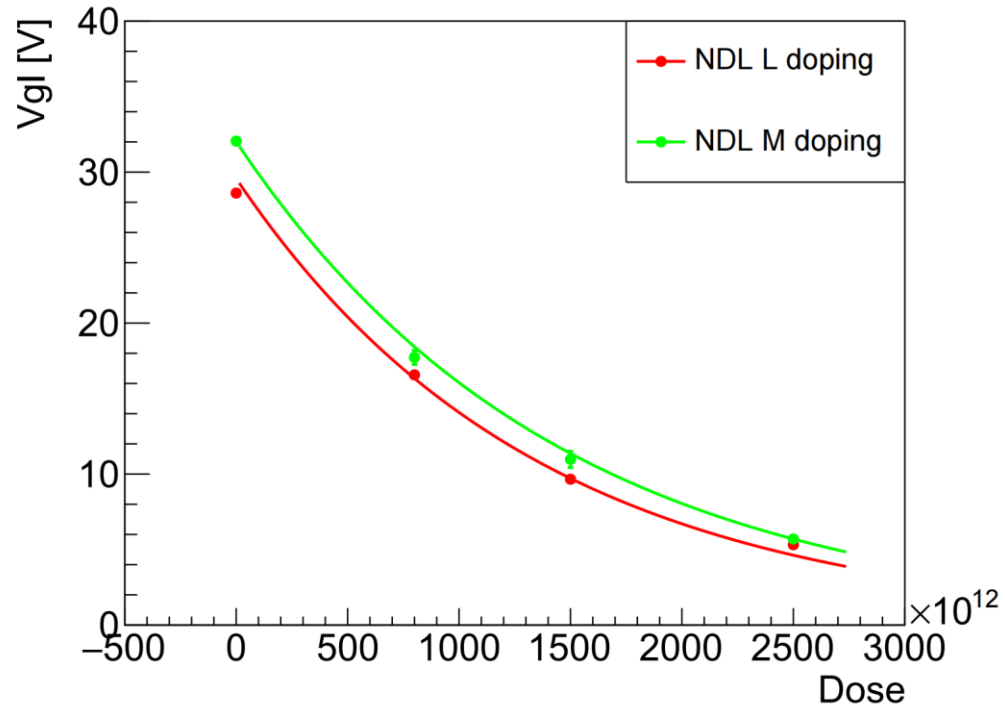
Pad leakage current (V <sub>bd</sub> condition)	< 500 nA
Breakdown voltage requirement	(V <sub>bd</sub> -V <sub>gl</sub> )/D>1.7 V/μm
Device leakage current	< 5 μA/cm <sup>2</sup> at bias voltage<V <sub>bd</sub>
V <sub>gl,pad</sub> spread over the sensor	(Max(V <sub>gl,pad</sub> )-Min(V <sub>gl,pad</sub> ))/<V <sub>gl,pad</sub> > <0.01
V <sub>bd,pad</sub> spread over the sensor	RMS(V <sub>bd,pad</sub> )/<V <sub>bd,pad</sub> > <0.05
Pad leakage current spread at 0.9·V <sub>bd</sub>	Peak-to-Peak within a factor of 3x

Hit efficiency at normal incidence (central part of pad)	> 97% (>95%) before (after) irradiation
Time resolution	<35 ps (<70 ps) before (after) irradiation
Power consumption at V <sub>op</sub>	< 100 mW/cm <sup>2</sup>
Total leakage current	<125 μA/cm <sup>2</sup>
Collected charge	>15 fC (start), >4 fC (end of lifetime)
Maximum pad leakage current	5 μA
Maximum bias voltage at the sensor	800 V



# NDL 传感器 --- 抗辐照性能

Fit the function using  $V_{gl} = \text{const} * \text{Exp}(-c \text{ factor} * \text{dose})$



	cons	err(cons)	c factor	err (c factor)
L doping	29.57	0.06	$7.422 \times 10^{-16}$	$0.016 \times 10^{-16}$
M doping	32.02	0.15	$6.905 \times 10^{-16}$	$0.023 \times 10^{-16}$

# PEB结构

